

P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY

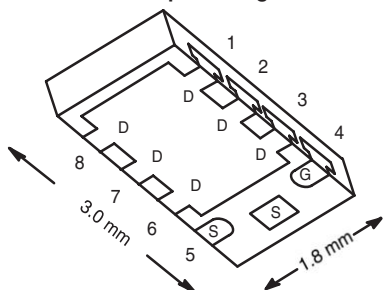
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ.)
- 20	0.022 at $V_{GS} = - 4.5$ V	- 12 ^a	20 nC
	0.029 at $V_{GS} = - 2.5$ V	- 12 ^a	
	0.041 at $V_{GS} = - 1.8$ V	- 12 ^a	

FEATURES

- Halogen-free
- TrenchFET® Power MOSFET
- New thermally Enhanced PowerPAK® ChipFET® Package
 - Small Footprint Area
 - Low On-Resistance
 - Thin 0.8 mm Profile

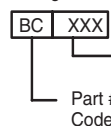

RoHS
COMPLIANT

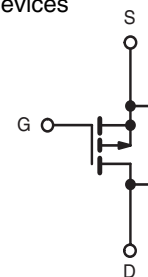
PowerPAK ChipFET Single



Bottom View

Marking Code


Lot Traceability
and Date Code

Part #
Code


Ordering Information: Si5481DU-T1-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	- 20	V
Gate-Source Voltage	V_{GS}	± 8	
Continuous Drain Current ($T_J = 150^\circ\text{C}$)	I_D	- 12 ^a	A
		- 12 ^a	
		- 9.7 ^{b, c}	
		- 7.8 ^{b, c}	
Pulsed Drain Current	I_{DM}	- 20	W
Continuous Source-Drain Diode Current	I_S	- 14.8	
		- 2.6 ^{b, c}	
Maximum Power Dissipation	P_D	17.8	
		11.4	
		3.1 ^{b, c}	
		2 ^{b, c}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	$^\circ\text{C}$
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, f}	R_{thJA}	30	40	$^\circ\text{C/W}$
Maximum Junction-to-Case (Drain)	R_{thJC}	5.5	7	

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

c. $t = 5$ s.

d. See Solder Profile (<http://www.vishay.com/ppg?73257>). The PowerPAK ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

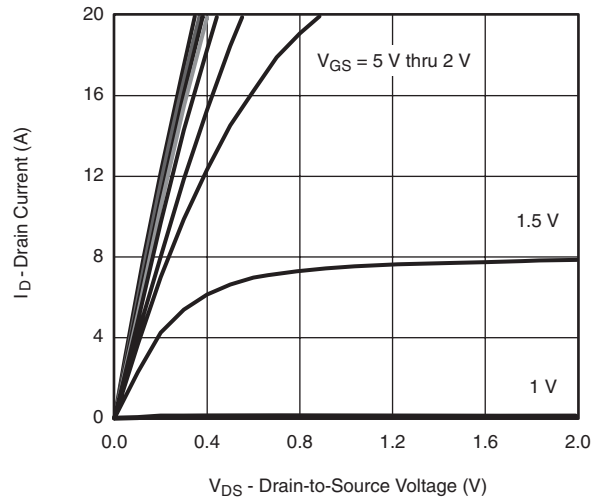
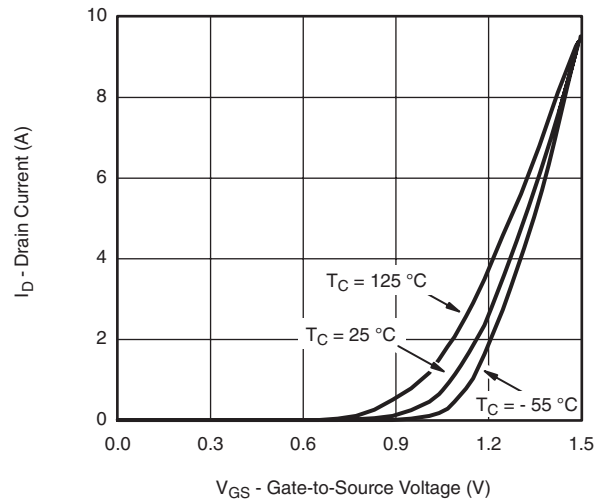
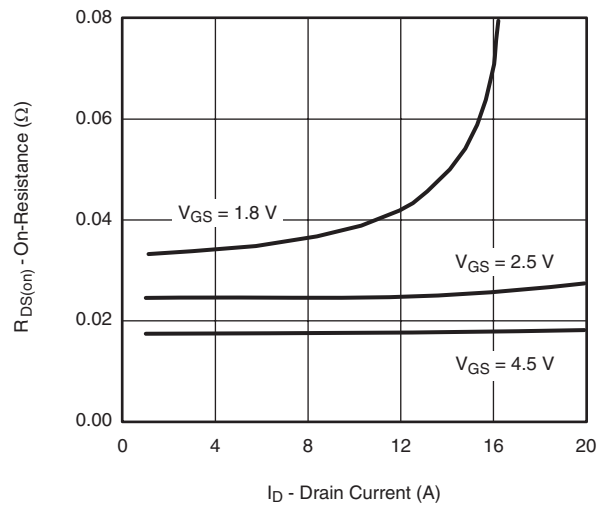
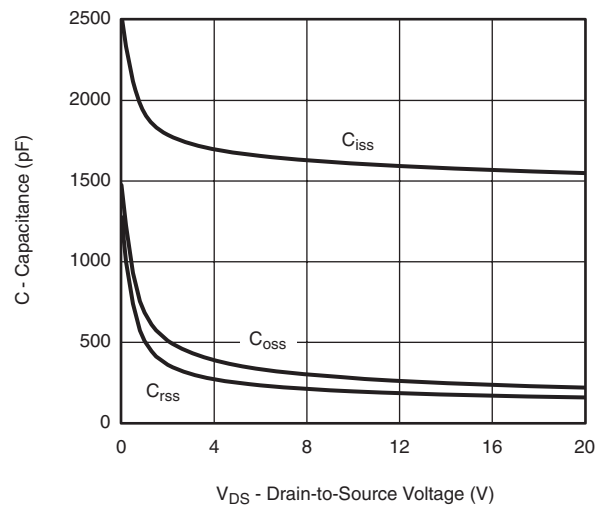
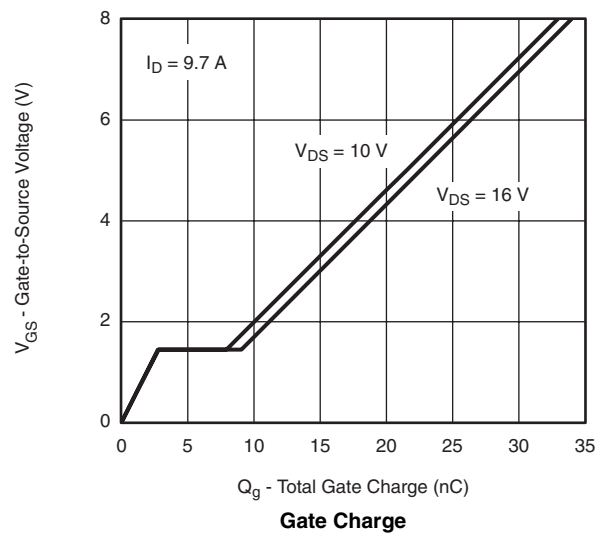
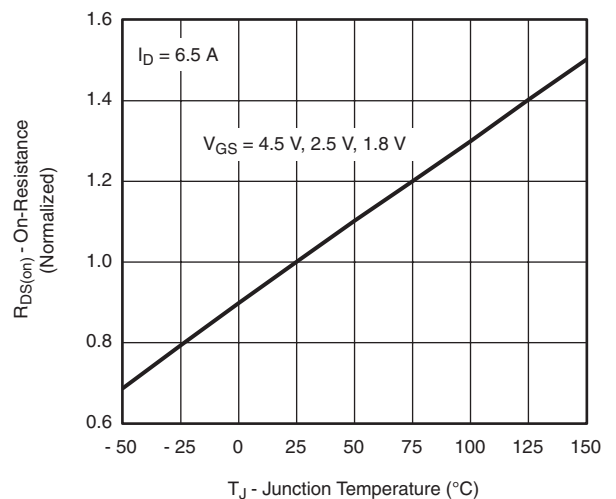
f. Maximum under steady state conditions is 90°C/W .

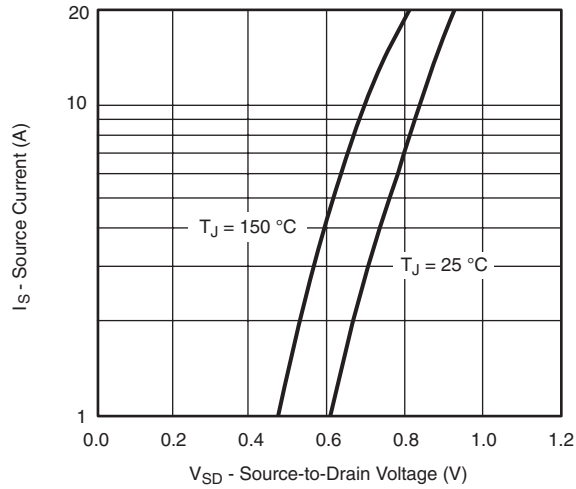
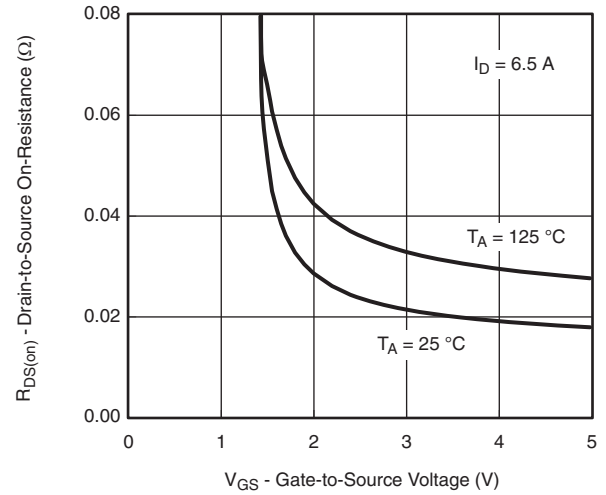
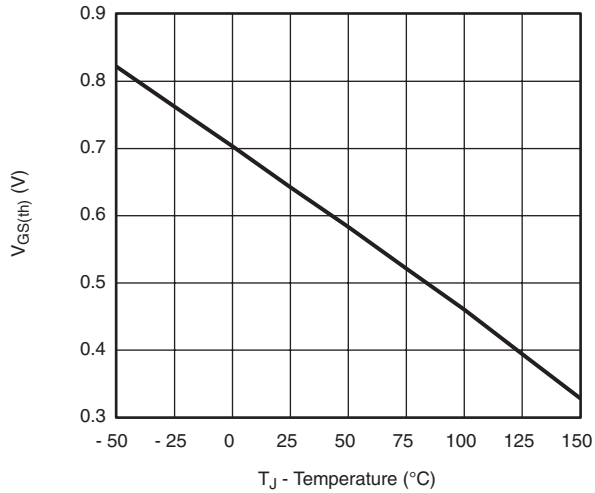
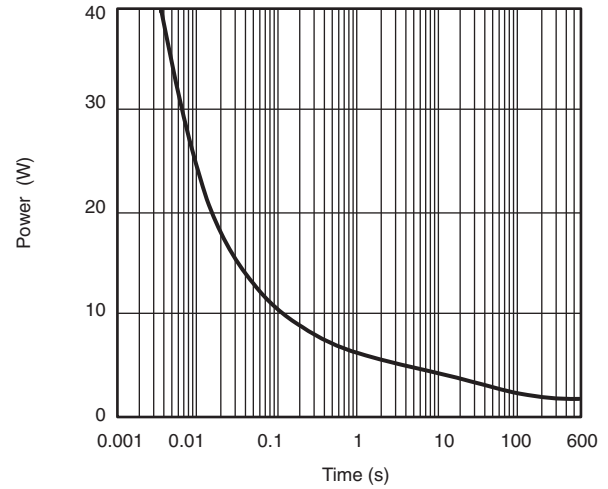
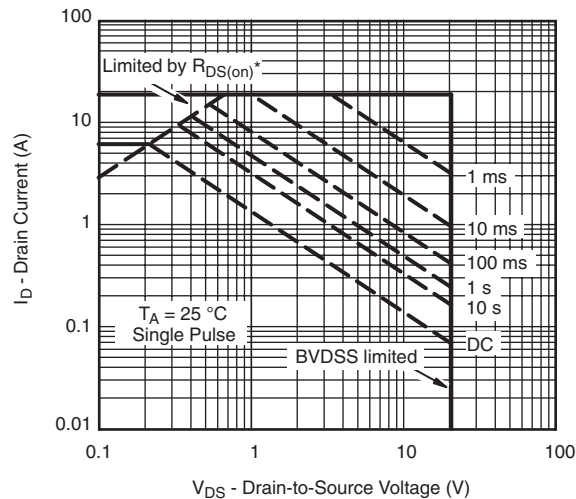
SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 20			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = - 250 μA		- 15.5		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			2.5		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 0.4		- 1	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 8 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 55 °C			- 10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≤ 5 V, V _{GS} = - 4.5 V	20			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 6.5 A		0.018	0.022	Ω
		V _{GS} = - 2.5 V, I _D = - 5.7 A		0.024	0.029	
		V _{GS} = - 1.8 V, I _D = 2.4 A		0.033	0.041	
Forward Transconductance ^a	g _{fs}	V _{DS} = - 10 V, I _D = - 6.5 A		25		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = - 10 V, V _{GS} = 0 V, f = 1 MHz		1610		pF
Output Capacitance	C _{oss}			300		
Reverse Transfer Capacitance	C _{rss}			200		
Total Gate Charge	Q _g	V _{DS} = - 10 V, V _{GS} = - 8 V, I _D = - 9.7 A		33	50	nC
		V _{DS} = - 10 V, V _{GS} = - 4.5 V, I _D = - 9.7 A		20	30	
Gate-Source Charge	Q _{gs}			2.8		
Gate-Drain Charge	Q _{gd}			5.1		
Gate Resistance	R _g	f = 1 MHz		8		Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 10 V, R _L = 1.3 Ω I _D ≡ - 7.8 A, V _{GEN} = - 4.5 V, R _g = 1 Ω		13	20	ns
Rise Time	t _r			50	75	
Turn-Off DelayTime	t _{d(off)}			90	135	
Fall Time	t _f			167	250	
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 10 V, R _L = 1.3 Ω I _D ≡ - 7.8 A, V _{GEN} = - 8 V, R _g = 1 Ω		6	15	
Rise Time	t _r			25	40	
Turn-Off DelayTime	t _{d(off)}			90	135	
Fall Time	t _f			167	250	
Drain-Source Body Diode Characteristics						
Continous Source-Drain Diode Current	I _S	T _C = 25 °C			- 14.8	A
Pulse Diode Forward Current ^a	I _{SM}				20	
Body Diode Voltage	V _{SD}	I _S = - 7.8 A, V _{GS} = 0 V		- 0.8	- 1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = - 7.8 A, di/dt = 100 A/μs, T _J = 25 °C		30	60	ns
Body Diode Reverse Recovery Charge	Q _{rr}			17	30	nC
Reverse Recovery Fall Time	t _a			14		ns
Reverse Recovery Rise Time	t _b			16		

Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

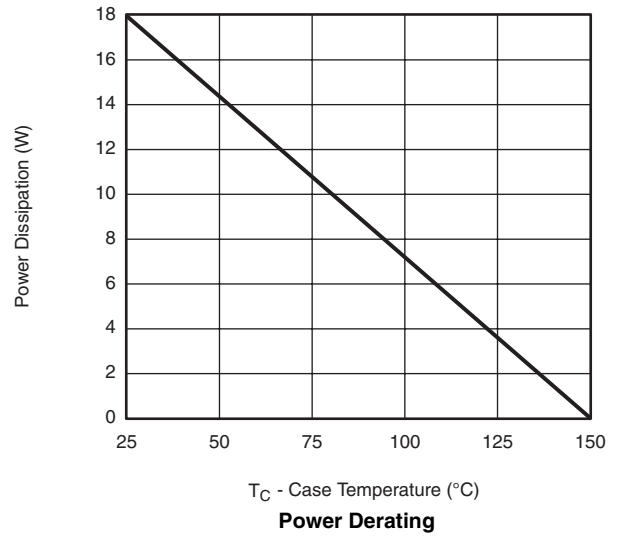
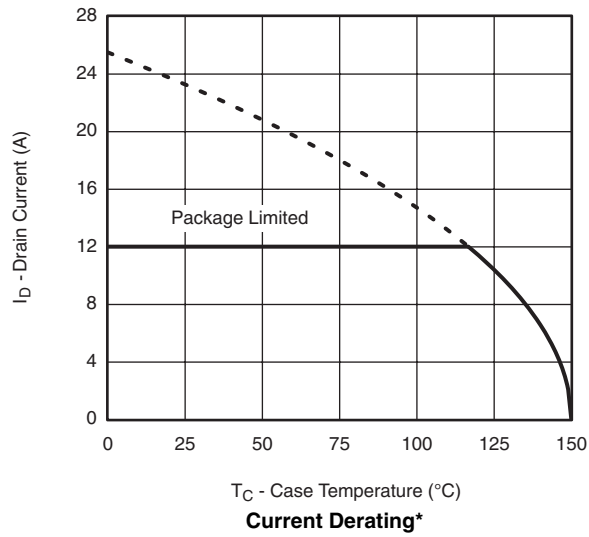
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** $T_A = 25^\circ\text{C}$, unless otherwise noted**Output Characteristics****Transfer Characteristics****On-Resistance vs. Drain Current and Gate Voltage****Capacitance****Gate Charge****On-Resistance vs. Junction Temperature**

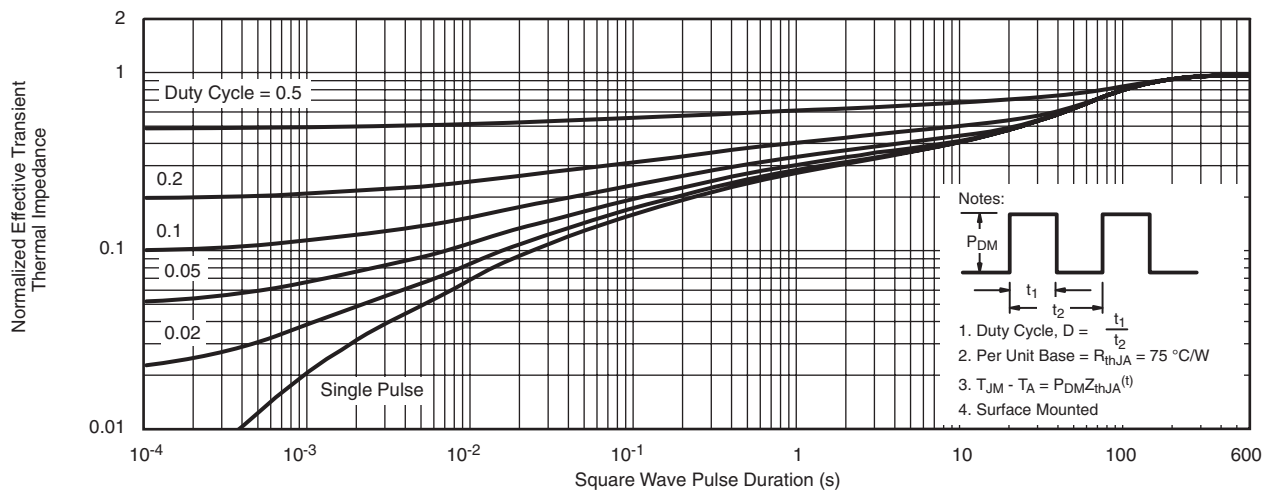
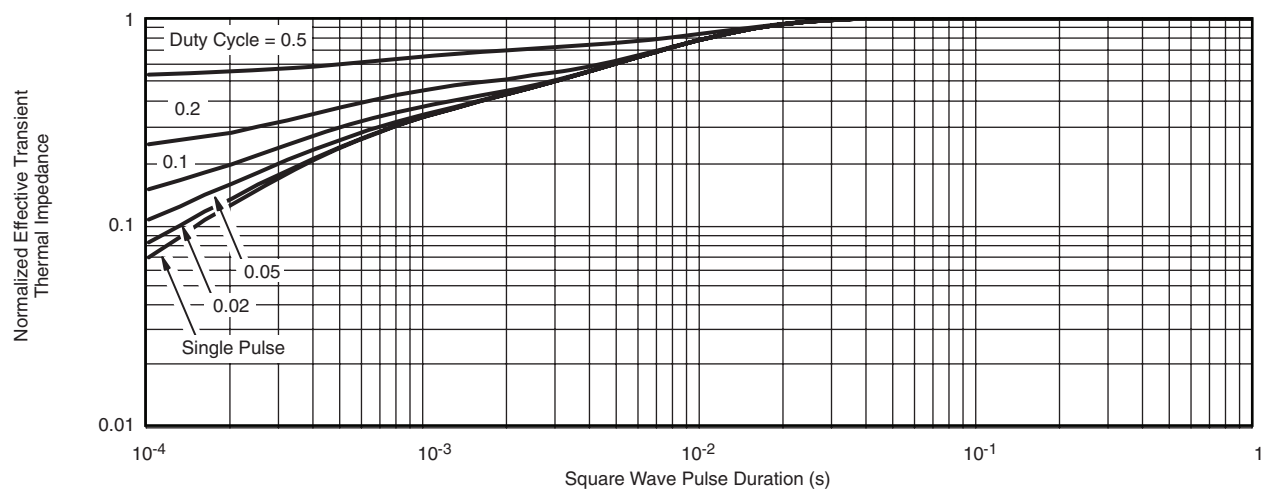
TYPICAL CHARACTERISTICS $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power, Junction-to-Ambient*** $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified**Safe Operating Area, Junction-to-Ambient**



TYPICAL CHARACTERISTICS $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted



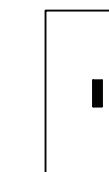
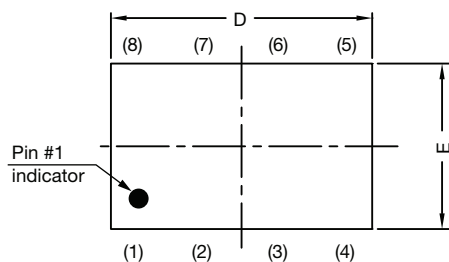
* The power dissipation P_D is based on $T_{J(max)} = 150\text{ }^{\circ}\text{C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted

Normalized Thermal Transient Impedance, Junction-to-Ambient

Normalized Thermal Transient Impedance, Junction-to-Case

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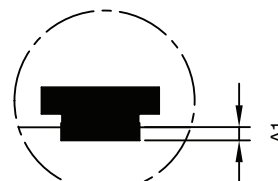
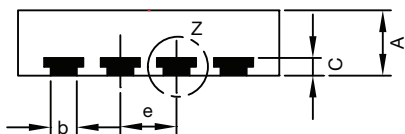
PowerPAK® ChipFET® Case Outline



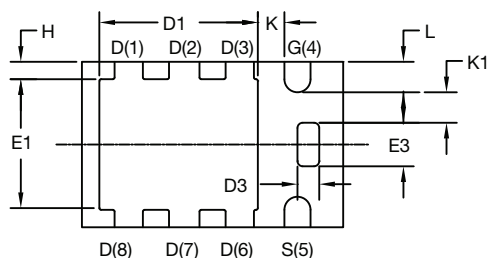
Side view of single



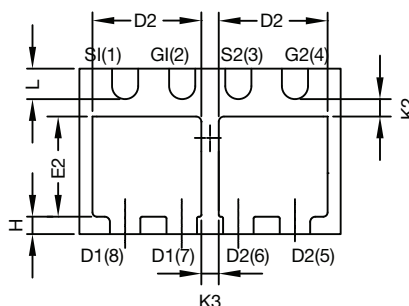
Side view of dual



Detail Z



Backside view of single pad



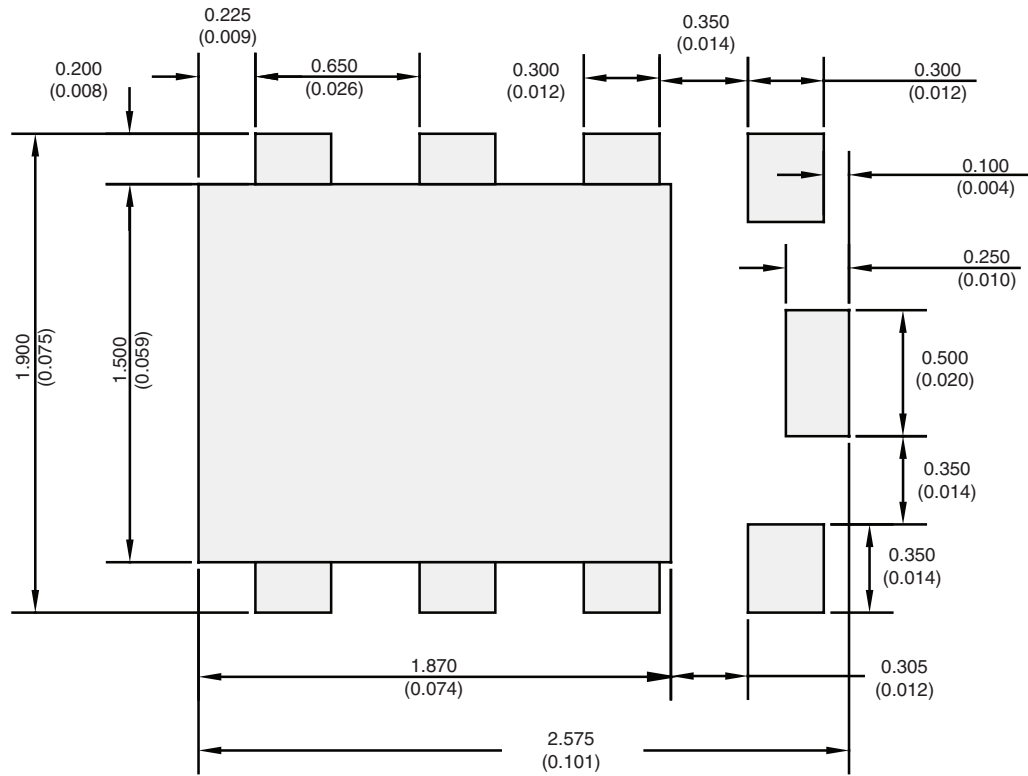
Backside view of dual pad

DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.70	0.75	0.85	0.028	0.030	0.033
A1	0	-	0.05	0	-	0.002
b	0.25	0.30	0.35	0.010	0.012	0.014
C	0.15	0.20	0.25	0.006	0.008	0.010
D	2.92	3.00	3.08	0.115	0.118	0.121
D1	1.75	1.87	2.00	0.069	0.074	0.079
D2	1.07	1.20	1.32	0.042	0.047	0.052
D3	0.20	0.25	0.30	0.008	0.010	0.012
E	1.82	1.90	1.98	0.072	0.075	0.078
E1	1.38	1.50	1.63	0.054	0.059	0.064
E2	0.92	1.05	1.17	0.036	0.041	0.046
E3	0.45	0.50	0.55	0.018	0.020	0.022
e	0.65 BSC			0.026 BSC		
H	0.15	0.20	0.25	0.006	0.008	0.010
K	0.25	-	-	0.010	-	-
K1	0.30	-	-	0.012	-	-
K2	0.20	-	-	0.008	-	-
K3	0.20	-	-	0.008	-	-
L	0.30	0.35	0.40	0.012	0.014	0.016
C14-0630-Rev. E, 21-Jul-14						
DWG: 5940						

Note

- Millimeters will govern

RECOMMENDED MINIMUM PADS FOR PowerPAK® ChipFET® Single



Recommended Minimum Pads
Dimensions in mm/(Inches)

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